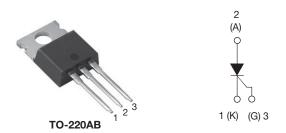


VS-25TTS...PbF Series, VS-25TTS...-M3 Series

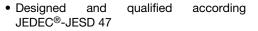
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Thyristor High Voltage, Phase Control SCR, 25 A



PRIMARY CHARACTERISTICS				
I _{T(AV)}	16 A			
V _{DRM} /V _{RRM}	800 V, 1200 V			
V _{TM}	1.25 V			
I _{GT}	45 mA			
TJ	-40 °C to 125 °C			
Package	TO-220AB			
Circuit configuration	Single SCR			

FEATURES





• 125 °C max. operating junction temperature

 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



APPLICATIONS

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge.

DESCRIPTION

The VS-25TTS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS						
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS						
Capacitive input filter T _A = 55 °C, T _J = 125 °C, common heatsink of 1 °C/W	18	22	А			

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
I _{T(AV)}	Sinusoidal waveform	16	А			
I _{RMS}		25	^			
V _{RRM} /V _{DRM}		800/1200	V			
I _{TSM}		320	Α			
V _T	16 A, T _J = 25 °C	1.25	V			
dV/dt		500	V/μs			
dl/dt		150	A/μs			
TJ		-40 to 125	°C			

VOLTAGE RATINGS							
V _{RRM} , MAXIMUM PEAK V _{DRM} , MAXIMUM PEAK I _{RRM} /I PART NUMBER REVERSE VOLTAGE DIRECT VOLTAGE AT 12 V V m/							
VS-25TTS08PbF, VS-25TTS08-M3	800	800	10				
VS-25TTS12PbF, VS-25TTS12-M3	1200	1200	10				



VS-25TTS...PbF Series, VS-25TTS...-M3 Series

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ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CO.	NDITIONS	VAL	UNITS		
PARAMETER	STINIBUL	IESI CO	RIDITIONS	TYP.	MAX.		
Maximum average on-state current	I _{T(AV)}	T _C = 93 °C, 180° conduc	tion half sine wave	1	6		
Maximum RMS on-state current	I _{RMS}			2	5	Α	
Maximum peak, one-cycle,	L	10 ms sine pulse, rated \	V _{RRM} applied	2	70	_ ^	
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no volt	tage reapplied	3	20		
Maximum I ² t for fusing	I ² t	10 ms sine pulse, rated V _{RRM} applied			365		
Maximum i-t for fusing	I-ι	10 ms sine pulse, no voltage reapplied		515		– A ² s	
Maximum $I^2\sqrt{t}$ for fusing	I²√t	t = 0.1 to 10 ms, no volta	ge reapplied	51	52	A²√s	
Maximum on-state voltage drop	V_{TM}	16 A, T _J = 25 °C	16 A, T _J = 25 °C			V	
On-state slope resistance	r _t	T 405.00			2.0	mΩ	
Threshold voltage	V _{T(TO)}	T _J = 125 °C		1	.0	V	
Maximum reverse and direct leakage current	1/1	T _J = 25 °C	V Potod V //	0	.5		
Maximum reverse and direct leakage current	I_{RM}/I_{DM}	$V_R = Rated V_{RRM}/V_{DRM}$		1	0		
Holding current	l _Η	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C		-	150	mA	
Maximum latching current	l∟	Anode supply = 6 V, resistive load, T _J = 25 °C			00		
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80$	Open 500		V/µs		
Maximum rate of rise of turned-on current	dl/dt			1	50	A/µs	

TRIGGERING	TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum peak gate power	P _{GM}		8.0	w			
Maximum average gate power	P _{G(AV)}		2.0	VV			
Maximum peak positive gate current	+ I _{GM}		1.5	Α			
Maximum peak negative gate voltage	- V _{GM}		10	V			
	I _{GT}	Anode supply = 6 V, resistive load, T _J = - 10 °C	60				
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T _J = 25 °C	45	mA			
		Anode supply = 6 V, resistive load, T _J = 125 °C	20				
		Anode supply = 6 V, resistive load, T _J = - 10 °C	2.5				
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	2.0	V			
voltage to trigger		Anode supply = 6 V, resistive load, T _J = 125 °C	1.0	V			
Maximum DC gate voltage not to trigger	$V_{\sf GD}$	T 105 % V Detectively	0.25				
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = Rated value	2.0	mA			

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9		
Typical reverse recovery time	t _{rr}	T _J = 125 °C	4	μs	
Typical turn-off time	t _q	1	110		

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THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T_J , T_{Stg}		-40 to 125	°C
Maximum thermal resistance, junction to case		R_{thJC}	DC operation	1.1	
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	OZ.
Mounting torque minimum maximum				6 (5)	kgf · cm
				12 (10)	(lbf · in)
Madiandada			Occasional TO COOME	25TTS08	
Marking device		Case style TO-220AB	25TTS12		

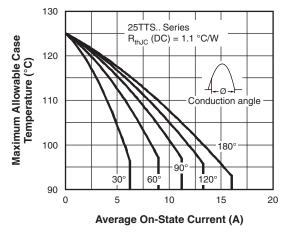


Fig. 1 - Current Rating Characteristics

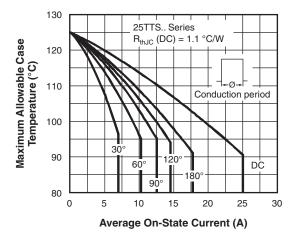


Fig. 2 - Current Rating Characteristics

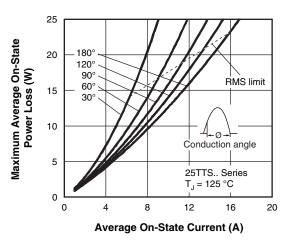


Fig. 3 - On-State Power Loss Characteristics

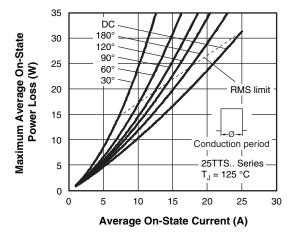


Fig. 4 - On-State Power Loss Characteristics

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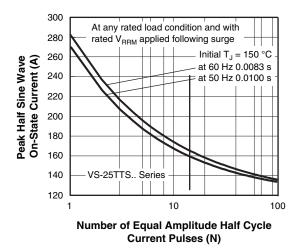


Fig. 5 - Maximum Non-Repetitive Surge Current

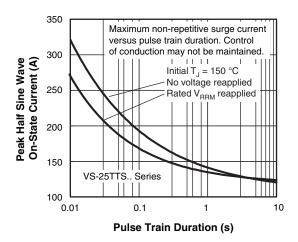


Fig. 6 - Maximum Non-Repetitive Surge Current

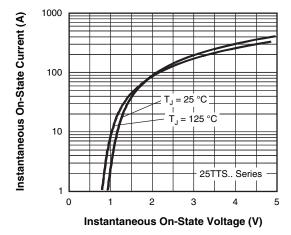


Fig. 7 - On-State Voltage Drop Characteristics

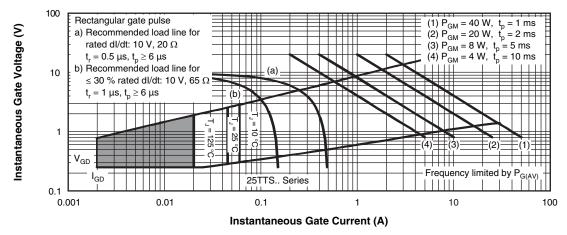


Fig. 8 - Gate Characteristics

VS-25TTS...PbF Series, VS-25TTS...-M3 Series

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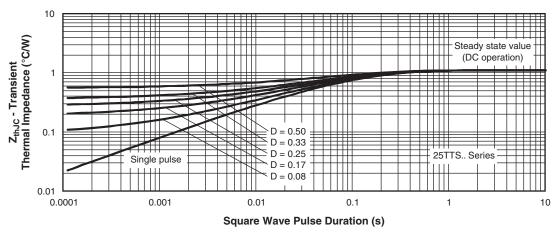


Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE

	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	0.5	_	_		40	DI E
Device code	VS-	25	Т	Т	S	12	PbF
		(2)	(3)	(4)	(5)	(6)	(7)
	1	- Vish	nay Sem	niconduc	ctors pro	duct	
	2	- Cur	rent rati	ng (25 =	25 A)		
	3	- Circ	uit conf	iguratior	1:		
		T =	Single t	hyristor			
	4	- Pac	kage:				
		T =	TO-220	AB			
	5	- Тур	e of silic	con:			
				rd recov	ery recti	fier	08
		- Volt	age rati	ng —			12
	7	- Envi	ronmen	tal digit:			
		PbF	= Lead	(Pb)-fre	e and R	oHS co	mpliant

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-25TTS08PbF	50	1000	Antistatic plastic tubes			
VS-25TTS08-M3	50	1000	Antistatic plastic tubes			
VS-25TTS12PbF	50	1000	Antistatic plastic tubes			
VS-25TTS12-M3	50	1000	Antistatic plastic tubes			

-M3 = Halogen-free, RoHS compliant, and terminations lead (Pb)-free

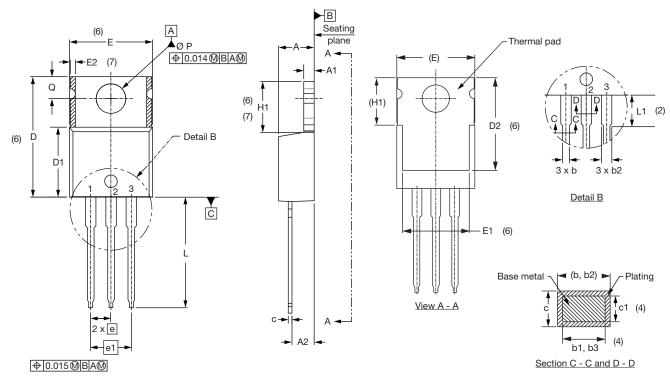
LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95222</u>					
Part marking information	TO-220AB PbF	www.vishay.com/doc?95225			
Part marking information	TO-220AB -M3	www.vishay.com/doc?95028			



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TO-220AB

DIMENSIONS in millimeters and inches



Lead tip

Lead assignments

<u>Diodes</u>

- 1. Anode/open
- 2. Cathode
- 3. Anode

Conforms to JEDEC outline TO-220AB

SYMBOL	MILLIN	IETERS	INCHES		NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
Е	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° to 93°		90° to 93°		

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline



Legal Disclaimer Notice

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